

30V N-Channel MOSFET

Product Summary

V(BR)DSS	R _{DS(on)MAX}	l _D	
	35mΩ@10V		
30V	40mΩ@4.5V	5.8A	
	52mΩ@2.5V		

Feature

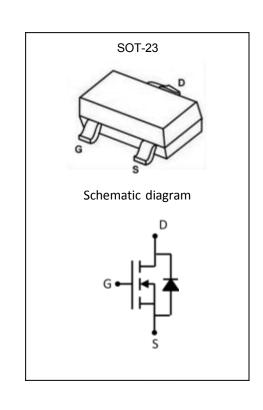
- TrenchFET Power MOSFET
- Excellent R_{DS(on)} and Low Gate Charge

Application

- DC/DC Converter
- Load Switch for Portable Devices
- Battery Switch

MARKING:





ABSOLUTE MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit				
Drain-Source Voltage	V _{DS}	30	V				
Gate-Source Voltage	Vgs	±12	V				
Continuous Drain Current	ID	5.8	Α				
Pulsed Drain Current ⁽¹⁾	I _{DM}	30	Α				
Power Dissipation	PD	0.35	W				
Thermal Resistance from Junction to Ambient ⁽²⁾	Reja	357	°C/W				
Junction Temperature	TJ	-55~ +150	$^{\circ}$				
Storage Temperature	T _{STG}	-55~ +150	$^{\circ}$ C				



MOSFET ELECTRICAL CHARACTERISTICS(Ta=25℃ unless otherwise noted)

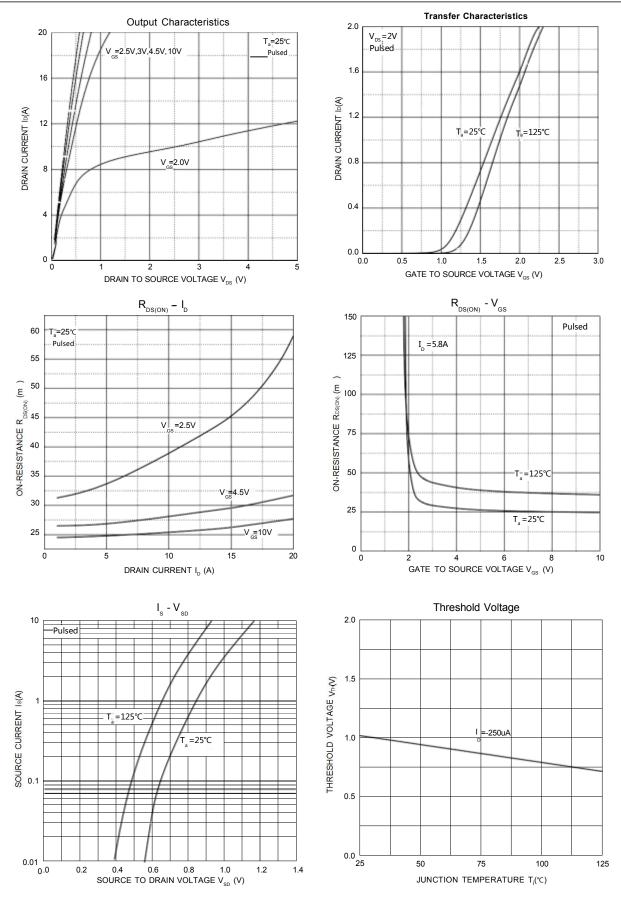
Parameter	Symbol	Test Condition	Min	Туре	Max	Unit
Static Characteristics			·			
Drain-source breakdown voltage	V(BR)DSS	V _{GS} = 0V, I _D =250μA	30			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =24V,V _{GS} = 0V			1	μA
Gate-body leakage current	Igss	V _{GS} =±12V, V _{DS} = 0V			±0.1	μA
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	0.7		1.4	V
		V _{GS} =10V, I _D =5.8A		27	35	
Drain-source on-resistance(3)	R _{DS(on)}	V _{GS} =4.5V, I _D =5A		29	40	mΩ
		V _{GS} =2.5V, I _D =4A		38	52	
Forward tranconductance	g FS	V _{DS} =5V, I _D =5A	8			S
Dynamic characteristics(4)	'					
Input Capacitance	Ciss				1050	
Output Capacitance	Coss	V _{DS} =15V,V _{GS} =0V,f =1MHz		99		pF
Reverse Transfer Capacitance	Crss			77		
Gate resistance	Rg	V _{DS} =0V,V _{GS} =0V, f=1MHz			3.6	Ω
Switching Characteristics ⁽⁴⁾	•		·			
Turn-on delay time	t _{d(on)}				5	
Turn-on rise time	tr	Vgs=10V,Vps=15V,			7	
Turn-off delay time	t _{d(off)}	$RL=2.7\Omega,R_{GEN}=3\Omega$			40	ns
Turn-off fall time	tf				6	
Source-Drain Diode characteristics	•		•			
Diode Forward voltage(3)	V _{DS}	V _{GS} =0V, I _S =1A			1	V

Note:

- 1. Repetitive Rating : Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t < 5 sec.
- 3. Pulse Test : Pulse Width≤300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production testing.



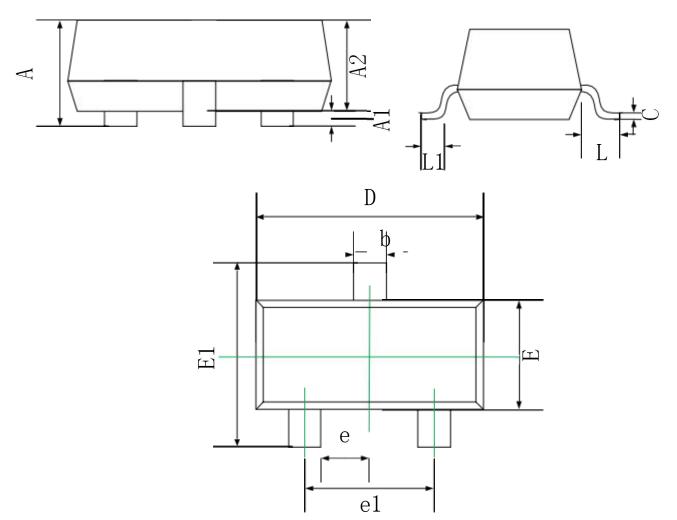
Typical Electrical and Thermal Characteristics



REV: AO AUG. 2021



SOT-23 Package Information

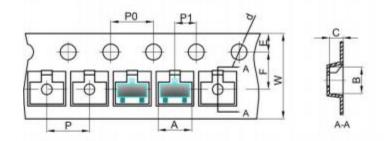


C: make al	Dimensions In Millimeters					
Symbol	Min.	Max.				
Α	0.90	1.15				
A1	0.00	0.10				
A2	0.90	1.05				
b	0.30	0.50				
С	0.08 0.15					
D	2.80 3.00					
E	1.20 1.40					
E1	2.25	2.55				
е	0.95 REF.					
e1	1.80 2.00					
L	0.55	REF.				
L1	0.30	0.50				

SOT-23 Tape and Reel

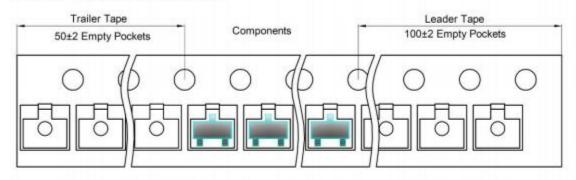
SOT-23 Tape and reel

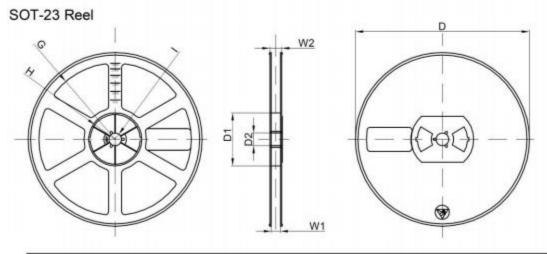
SOT-23 Embossed Carrier Tape



Dimensions are in millimeter										
Pkg type	A	В	С	d	E	F	P0	Р	P1	W
SOT-23	3.15	2.77	1.22	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

SOT-23 Tape Leader and Trailer





Dimensions are in millimeter									
Reel Option	D	D1	D2	G	н	E.	W1	W2	
7°Dia	Ø178.00	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30	

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	30,000 pcs	203×203×195	120,000 pcs	438×438×220	



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